

Low Voltage Standard Rectifier

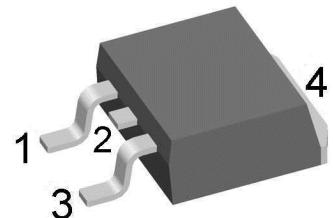
V_{RRM} = 800 V
 I_{FAV} = 20 A
 V_F = 1.22 V

Single Diode

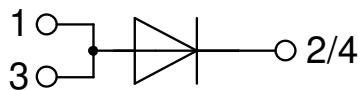
Part number

DLA20IM800PC

Marking on Product: *DLA20IM800PC*



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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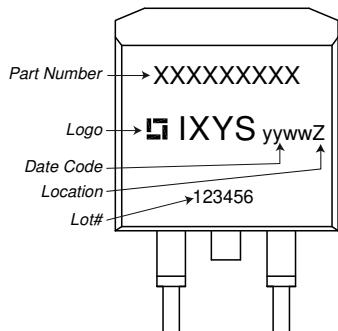
Rectifier

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			900	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^\circ\text{C}$			800	V
I_R	reverse current	$V_R = 800 \text{ V}$ $V_R = 800 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		5 0.05	μA mA
V_F	forward voltage drop	$I_F = 20 \text{ A}$ $I_F = 40 \text{ A}$ $I_F = 20 \text{ A}$ $I_F = 40 \text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$		1.25 1.49 1.22 1.54	V V V V
I_{FAV}	average forward current	$T_C = 140^\circ\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^\circ\text{C}$		20	A
V_{F0} r_F	threshold voltage slope resistance } for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.88 17	V $\text{m}\Omega$
R_{thJC}	thermal resistance junction to case				1	K/W
R_{thCH}	thermal resistance case to heatsink			0.25		K/W
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$		150	W
I_{FSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		200 215 170 185	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$ $t = 10 \text{ ms}; (50 \text{ Hz}), \text{sine}$ $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{sine}$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0 \text{ V}$ $T_{VJ} = 150^\circ\text{C}$ $V_R = 0 \text{ V}$		200 190 145 140	A^2s A^2s A^2s A^2s
C_J	junction capacitance	$V_R = 400 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$	7		pF

Package TO-263 (D2Pak)

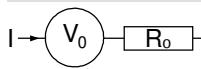
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				1.5		g
F_c	mounting force with clip		20		60	N

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

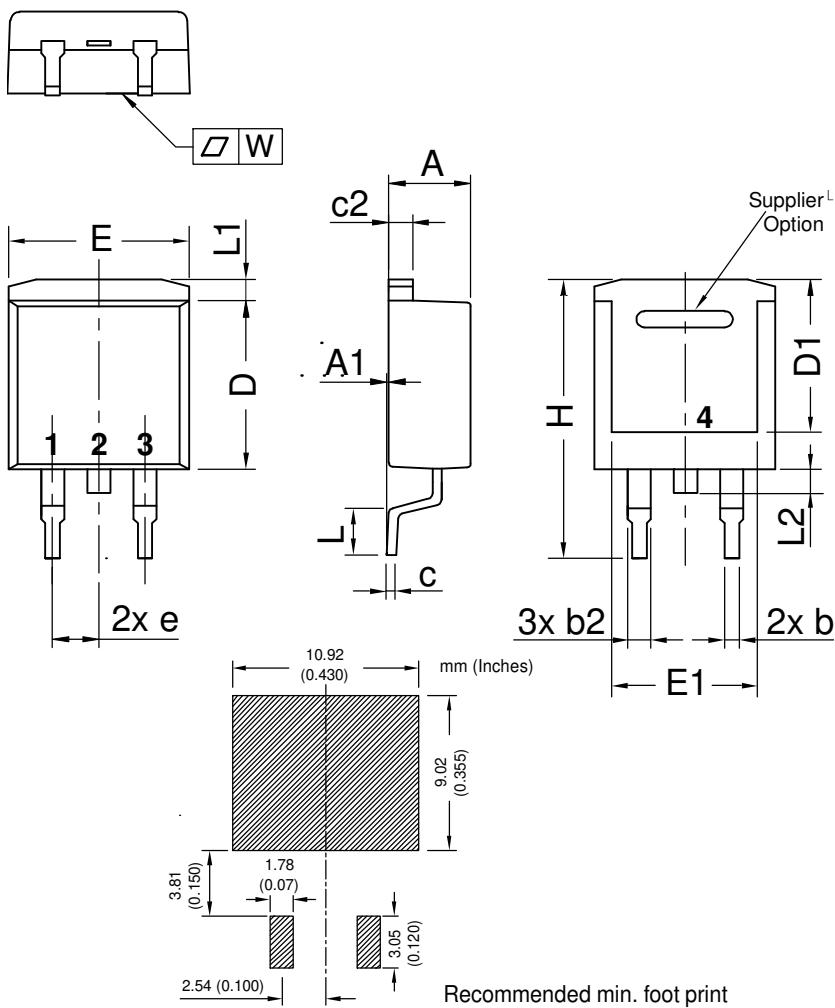
Product Marking

Part description

D = Diode
 L = Low Voltage Standard Rectifier
 A = (up to 1200V)
 20 = Current Rating [A]
 IM = Single Diode
 800 = Reverse Voltage [V]
 PC = TO-263AB (D2Pak) (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA20IM800PC-TRL	DLA20IM800PC	Tape & Reel	800	506475
Alternative	DLA20IM800PC-TUB	DLA20IM800PC	Tube	50	506628

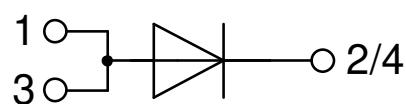
Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 175^\circ\text{C}$

Rectifier

$V_{0\max}$ threshold voltage 0.88 V
 $R_{0\max}$ slope resistance * 13 mΩ

Outlines TO-263 (D2Pak)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with
and/or within JEDEC standard.



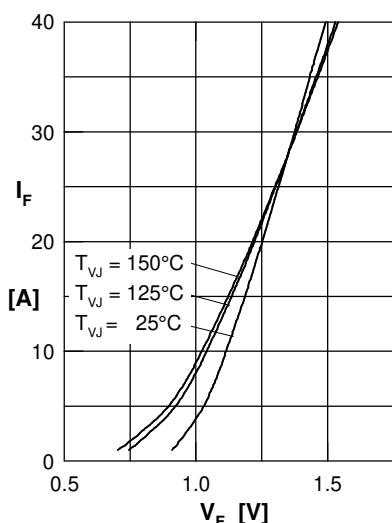
Rectifier


Fig. 1 Forward current versus voltage drop

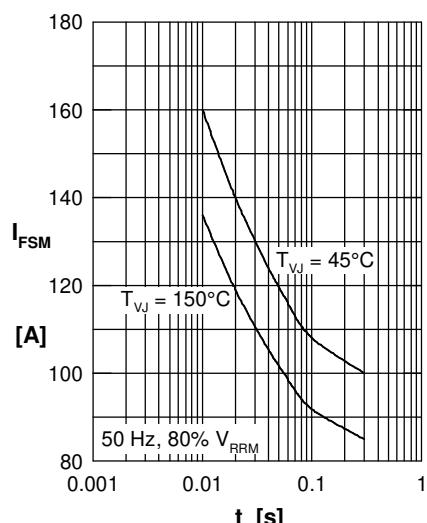


Fig. 2 Surge overload current

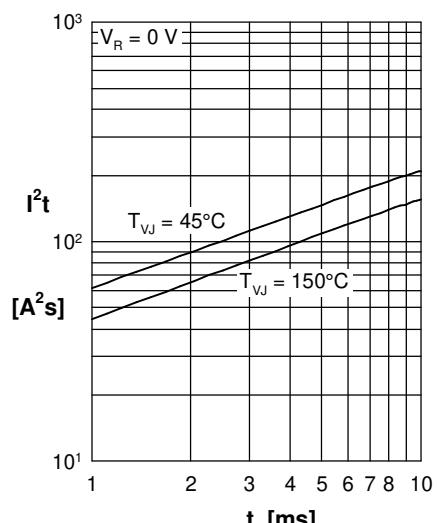
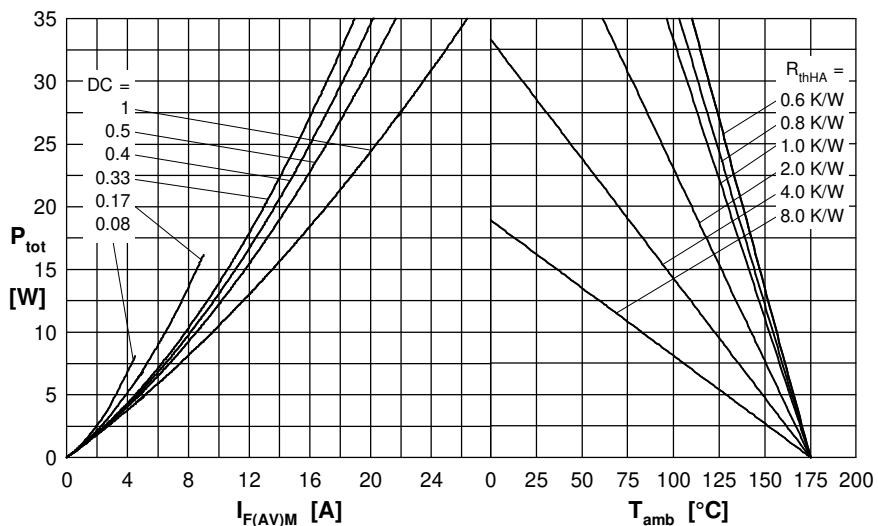

Fig. 3 I^2t versus time


Fig. 4 Power dissipation versus direct output current and ambient temperature

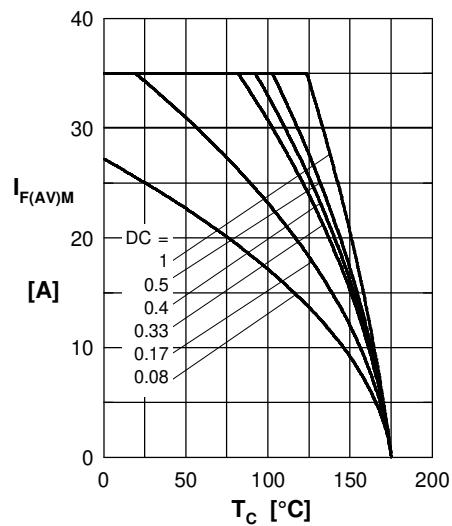


Fig. 5 Max. forward current vs. case temperature

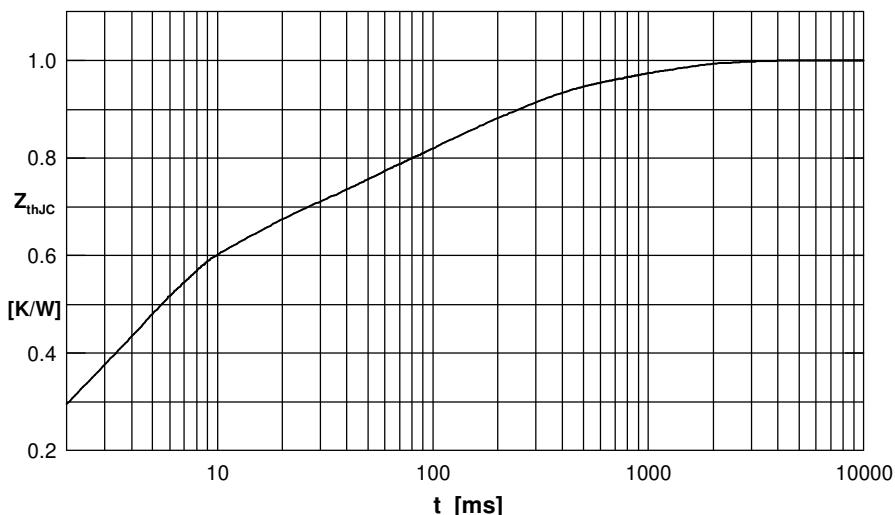


Fig. 6 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.51	0.0035
2	0.06	0.0003
3	0.14	0.0250
4	0.09	0.8000
5	0.20	0.1400